

CENTRAL INTELLIGENCE AGENCY

INFORMATION REPORT

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SECRET

COUNTRY	East Germany	REPORT	<input type="text"/>	25X1
SUBJECT	Silicon Transistors to be Developed at VEB Werk fuer Fernmeldewesen and VEB Carl von Ossietzky	DATE DISTR.	23 April 1954	
DATE OF INFO.	<input type="text"/>	NO. OF PAGES	1	
PLACE ACQUIRED	<input type="text"/>	REQUIREMENT	<input type="text"/>	25X1
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THE SOURCE EVALUATIONS IN THIS REPORT ARE DEFINITIVE.
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1. After development of germanium transistors was removed from VEB Werk fuer Fernmeldewesen, Berlin Oberschoeneweide, at the order of the Russians, the enterprise received in early March 1954 a development order from the East German government for silicon transistors. The development is under the direction of Dr. Boehm (fnu).
2. VEB Carl von Ossietzky (Dralowid), which is engaged in development of germanium transistors, also started development of silicon transistors in mid-February 1954.

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25 YEAR RE-REVIEW

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